

INCHANGE SEMICONDUCTOR

3

2.Collector

TO-3PN Package

G

R

MAX

20.30 15.50 15.70

4.90

1.10

2.10

3.60

3.20

3.40

mm

MIN

19.60

4.70

0.90

1.90

3.40

2.90

3.20

0.595 0.605

3.Emitter

PIN: 1.Base

С

isc Silicon PNP Power Transistors

MJE4350/4351/4352/4353

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В

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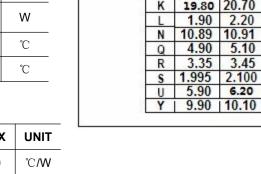
DESCRIPTION

- · Collector-Emitter Sustaining Voltage-
 - : V_{CEO(SUS)} = -100V(Min)- MJE4350
 - = -120V(Min)- MJE4351
 - = -140V(Min)- MJE4352
 - = -160V(Min)- MJE4353
- Low Saturation Voltage
- Complement to the NPN MJE4340/4341/4342/4343

APPLICATIONS

· Designed for use in high power audio amplifier applications and high voltage switching regulator circuits.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)								
SYMBOL	PARAMETEI	VALUE	UNIT					
V _{CBO}	Collector-Base Voltage	MJE4350	-100					
		MJE4351	-120	v				
		MJE4352	-140					
		MJE4353	-160	1				
V _{CEO}	Collector-Emitter Voltage	MJE4350	-100					
		MJE4351	-120	V				
		MJE4352	-140					
		MJE4353	-160					
V _{EBO}	Emitter-Base Voltage	-7	V					
lc	Collector Current-Continuous		-16	A				
Ісм	Collector Current-Peak		-20	A				
IB	Base Current-Continuous		-5	A				
Pc	Collector Power Dissipation @ $T_c=25^{\circ}C$		125	W				
TJ	Junction Temperature	150	°C					
T _{stg}	Storage Temperature Ra	-65~150	°C					



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case		°C/W

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MJE4350/4351/4352/4353

ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}		MJE4350	- I _C = -50mA ;I _B = 0	-100		V
	Collector-Emitter Sustaining Voltage	MJE4351		-120		
		MJE4352		-140		
		MJE4353		-160		
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage		I _C = -8A; I _B = -0.8A		-2.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage		I _C = -16A; I _B = -2A		-3.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage		I _C = -16A; I _B = -2A		-3.9	V
$V_{\text{BE(on)}}$	Base-Emitter On Voltage		I _C = -16A; V _{CE} = -4V		-3.9	V
I _{CEO}	Collector Cutoff Current	MJE4350	V _{CE} = -100V; I _B = 0		-0.75	- mA
		MJE4351	V _{CE} = -120V; I _B = 0		-0.75	
		MJE4352	V _{CE} = -140V; I _B = 0	-	-0.75	
		MJE4353	V _{CE} = -160V; I _B = 0	-	-0.75	
I _{CBO}	Collector Cutoff Current		V_{CB} = Rated V_{CB} ; I _E =0		-0.75	mA
Іево	Emitter Cutoff Current		V _{EB} = -7V; I _C =0		-1.0	mA
h _{FE-1}	DC Current Gain		I _C = -8A; V _{CE} = -2V	15		
h _{FE-2}	DC Current Gain		I _C = -16A; V _{CE} = -4V	8		

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